Product data sheet

1. General description

NPN low V_{CEsat} transistor in a SOT89 (SC-62) medium power and flat lead plastic package.

PNP complement: PBSS5480X

2. Features and benefits

- High h_{FE} and low V_{CEsat} at high current operation
- · High collector current capability: IC maximum 4 A
- · High efficiency leading to less heat generation
- · AEC-Q101 qualified

3. Applications

- Medium power peripheral drivers; e.g. fan, motor
- · Strobe flash units for DSC and mobile phones
- · Inverter applications; e.g. TFT displays
- Power switch for LAN and ADSL systems
- Medium power DC-to-DC conversion
- Battery chargers

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base		-	-	80	V
I _C	collector current		[1]	-	-	4	Α
I _{CM}	peak collector current	limited by $T_{j(max)}$; single pulse; $t_p \le 1$ ms		-	-	10	Α
R _{CEsat}	collector-emitter saturation resistance	I_C = 5 A; I_B = 500 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C		-	40	54	mΩ

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².



80 V, 4 A NPN low VCEsat transistor

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	Е	emitter		С
2	С	collector		
3	В	base	3 2 1	В — , , , , , , , , , , , , , , , , , , ,
			SOT89	sym123

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PBSS4480X	SOT89	plastic, surface-mounted package; 3 leads; 1.5 mm pitch; 4.5 mm x 2.5 mm x 1.5 mm body	SOT89

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PBSS4480X	%1Y

[1] % = placeholder for manufacturing site code

80 V, 4 A NPN low VCEsat transistor

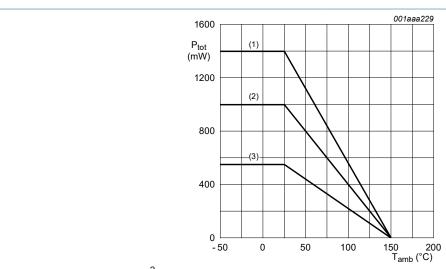
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	80	V
V _{CEO}	collector-emitter voltage	open base		-	80	V
V _{EBO}	emitter-base voltage	open collector		-	5	V
I _C	collector current		[1]	-	4	Α
I _{CRM}	repetitive peak collector current	t _p ≤ 10 ms		-	6	А
I _{CM}	peak collector current	limited by $T_{j(max)}$; single pulse; $t_p \le 1$ ms		-	10	Α
I _B	base current			-	1	Α
I _{BM}	peak base current	single pulse; t _p ≤ 300 µs		-	2	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[2] [3]	-	2.5	W
			[2]	-	550	mW
			[4]	-	1	W
			[1]	-	1.4	W
			[5]	-	1.6	W
T _j	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [2] [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Operated under pulsed conditions; $t_p \le 10$ ms; $\delta \le 0.2$.
- [4] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- Device mounted on a 7 cm² ceramic PCB, 1 cm² single-sided copper and tin-plated. [5]



- (1) FR4 PCB; 6 cm² mounting pad for collector (2) FR4 PCB; 1 cm² mounting pad for collector
- (3) FR4; standard footprint

Power derating curves Fig. 1.

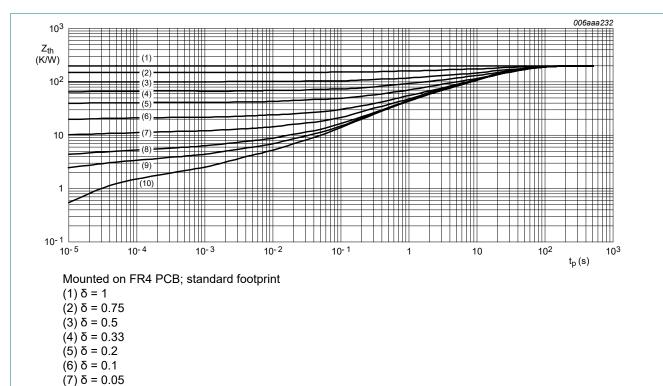
80 V, 4 A NPN low VCEsat transistor

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from	[1] [1] [2] [3] [4] [5]	[1] [2]	-	-	50	K/W
	junction to ambient		[1]	-	-	225	K/W
			[3]	-	-	125	K/W
			[4]	-	-	90	K/W
			[5]	-	-	80	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	16	K/W

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Operated under pulsed conditions; $t_p \le 10$ ms; $\delta \le 0.2$.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm² [3]
- [4] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- Device mounted on a 7 cm² ceramic PCB, 1 cm² single-sided copper and tin-plated.



 $(9) \delta = 0.01$

 $(10) \delta = 0$

 $(8) \delta = 0.02$

Transient thermal impedance as a function of pulse duration; typical values

80 V, 4 A NPN low VCEsat transistor

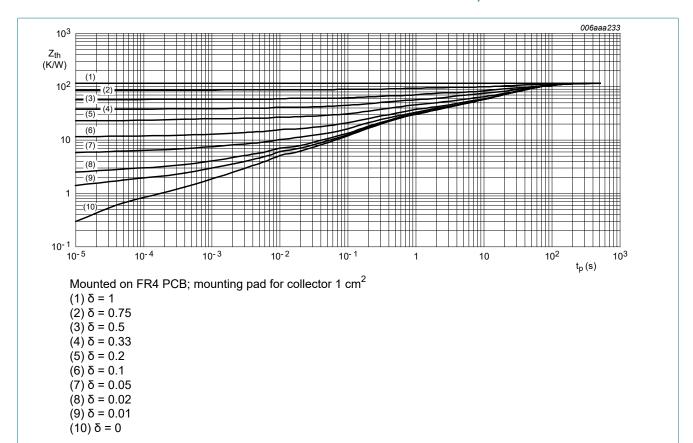
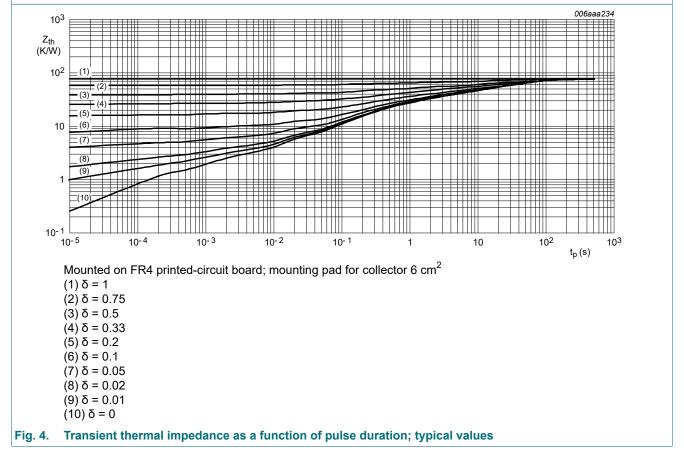


Fig. 3. Transient thermal impedance as a function of pulse duration; typical values



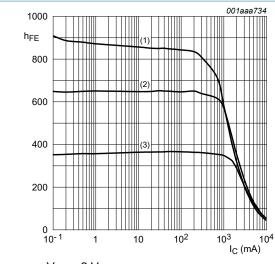
80 V, 4 A NPN low VCEsat transistor

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = 80 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
	current	V _{CB} = 80 V; I _E = 0 A; T _j = 150 °C	-	-	50	μΑ
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	100	nA
I _{CES}	collector-emitter cut-off current	V _{CE} = 80 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	100	nA
h _{FE}	DC current gain	V _{CE} = 2 V; I _C = 0.5 A; T _{amb} = 25 °C	250	400	-	
		V_{CE} = 2 V; I_{C} = 1 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	250	400	-	
		V_{CE} = 2 V; I_{C} = 2 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	175	270	-	
		V_{CE} = 2 V; I_{C} = 4 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	80	140	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 0.5 \text{ A}; I_B = 50 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$	-	25	40	mV
		I _C = 1 A; I _B = 50 mA; T _{amb} = 25 °C	-	55	80	mV
		I _C = 2 A; I _B = 40 mA; T _{amb} = 25 °C	-	110	160	mV
		I_C = 4 A; I_B = 200 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	170	230	mV
		$I_C = 5 \text{ A}$; $I_B = 500 \text{ mA}$; pulsed; $t_p \le$	-	200	270	mV
R _{CEsat}	collector-emitter saturation resistance	300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	40	54	mΩ
V _{BEsat}	base-emitter saturation	$I_C = 0.5 \text{ A}; I_B = 50 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$	-	0.78	0.85	V
	voltage	I _C = 1 A; I _B = 50 mA; T _{amb} = 25 °C	-	0.79	0.9	V
		I_C = 1 A; I_B = 100 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	0.82	0.95	V
		I_C = 4 A; I_B = 400 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	0.95	1.05	V
V_{BEon}	base-emitter turn-on voltage	V _{CE} = 2 V; I _C = 2 A; T _{amb} = 25 °C	-	0.78	0.85	V
f _T	transition frequency	V _{CE} = 10 V; I _C = 100 mA; f = 100 MHz; T _{amb} = 25 °C	120	150	-	MHz
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A}; f = 1 \text{ MHz}; $ $T_{amb} = 25 ^{\circ}\text{C}$	-	35	50	pF

80 V, 4 A NPN low VCEsat transistor

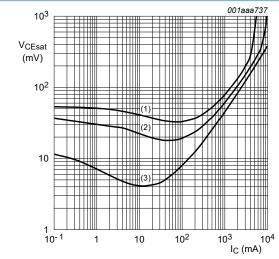


$$V_{CE} = 2 V$$

$$(1) T_{amb} = 100 ° ($$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

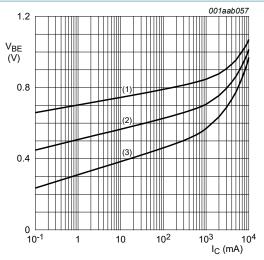
Fig. 5. DC current gain as a function of collector current; typical values



 $⁽¹⁾ I_C/I_B = 100$

(3)
$$I_C/I_B = 10$$

Collector-emitter saturation voltage as a Fig. 7. function of collector current; typical values

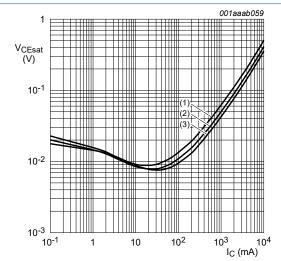


$$V_{CF} = 2 V$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 6. Base-emitter voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 20$$

$$(1) T_{amb} = 100 °C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

$$(3) T_{amb} = -55 °C$$

Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values

7 / 13

⁽²⁾ $I_C/I_B = 50$

80 V, 4 A NPN low VCEsat transistor

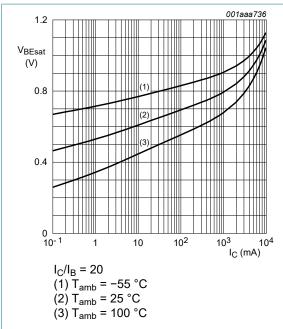
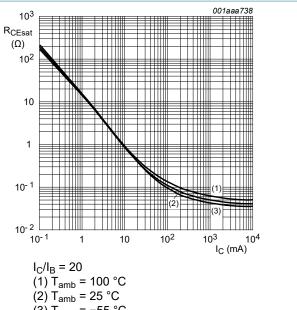


Fig. 9. collector current; typical values



(1) $T_{amb} = 100 \text{ °C}$ (2) $T_{amb} = 25 \text{ °C}$ (3) $T_{amb} = -55 \text{ °C}$

Base-emitter saturation voltage as a function of Fig. 10. Equivalent on-resistance as a function of collector current; typical values

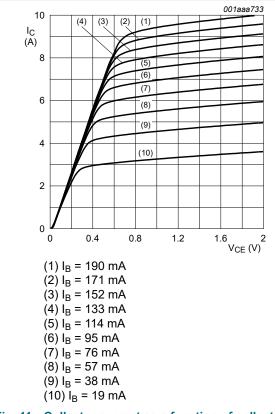
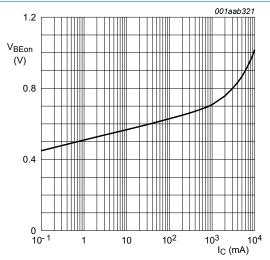


Fig. 11. Collector current as a function of collectoremitter voltage; typical values



 T_{amb} = 25 °C

Fig. 12. Base-emitter turn-on voltage as a function of collector current; typical values

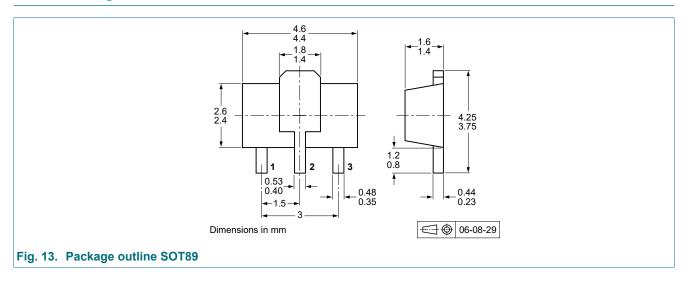
80 V, 4 A NPN low VCEsat transistor

11. Test information

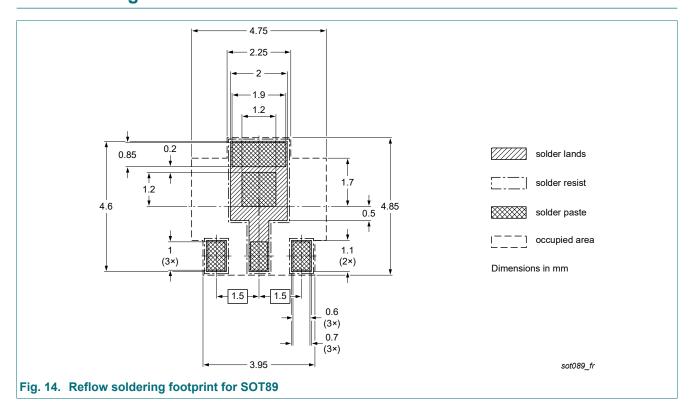
Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

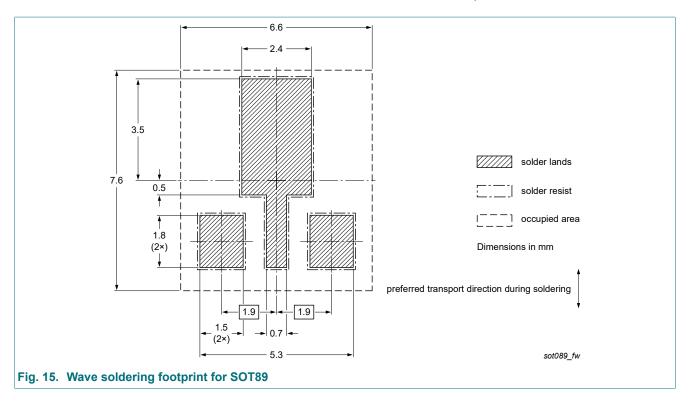
12. Package outline



13. Soldering



80 V, 4 A NPN low VCEsat transistor



80 V, 4 A NPN low VCEsat transistor

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PBSS4480X v.3	20240605	Product data sheet	-	PBSS4480X v.2		
Modifications:	 The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia. Legal texts have been adapted to the new company name where appropriate. Section "Packing information" removed. 					
PBSS4480X v.2	20041025	Product data sheet	-	PBSS4480X v.1		
PBSS4480X v.1	20040805	Product data sheet	-	-		

80 V, 4 A NPN low VCEsat transistor

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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80 V, 4 A NPN low VCEsat transistor

Contents

1.	General description	1
2.	Features and benefits	1
3.	Applications	1
4.	Quick reference data	1
5.	Pinning information	2
6.	Ordering information	2
7.	Marking	2
8.	Limiting values	3
9.	Thermal characteristics	4
10.	. Characteristics	6
11.	Test information	9
12.	. Package outline	9
13.	. Soldering	9
14.	. Revision history	11
15.	. Legal information	12

For more information, please visit: http://www.nexperia.com
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